

# International IOR Rectifier

## MUR3020WTPbF

### Ultrafast Rectifier

#### Features

- Ultrafast Recovery Time
- Low Forward Voltage Drop
- Low Leakage Current
- 175°C Operating Junction Temperature
- Lead-Free ("PbF" suffix)

$$t_{rr} = 35\text{ns}$$

$$I_{F(AV)} = 30\text{Amp}$$

$$V_R = 200\text{V}$$

#### Description/ Applications

International Rectifier's MUR.. series are the state of the art Ultra fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultra fast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

#### Absolute Maximum Ratings

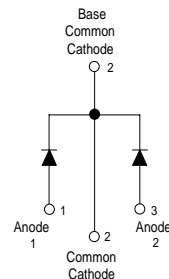
Parameters		Max	Units
$V_{RRM}$	Peak Repetitive Peak Reverse Voltage	200	V
$I_{F(AV)}$	Average Rectified Forward Current Per Leg	15	A
	Total Device, (Rated $V_R$ ), $T_C = 150^\circ\text{C}$ Total Device	30	
$I_{FSM}$	Non Repetitive Peak Surge Current Per Leg	200	
$I_{FM}$	Peak Repetitive Forward Current Per Leg (Rated $V_R$ , Square wave, 20 KHz), $T_C = 150^\circ\text{C}$	30	
$T_J, T_{STG}$	Operating Junction and Storage Temperatures	- 65 to 175	$^\circ\text{C}$

#### Case Styles

MUR3020WTPbF



TO247



**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Parameters	Min	Typ	Max	Units	Test Conditions
V <sub>BR</sub> , V <sub>r</sub> Breakdown Voltage, Blocking Voltage	200	-	-	V	I <sub>R</sub> = 100μA
V <sub>F</sub> Forward Voltage	-	-	1.05	V	I <sub>F</sub> = 15A
	-	-	0.85	V	I <sub>F</sub> = 15A, T <sub>J</sub> = 150°C
I <sub>R</sub> Reverse Leakage Current	-	-	10	μA	V <sub>R</sub> = V <sub>R</sub> Rated
	-	-	500	μA	T <sub>J</sub> = 150°C, V <sub>R</sub> = V <sub>R</sub> Rated
C <sub>T</sub> Junction Capacitance	-	55	-	pF	V <sub>R</sub> = 200V
L <sub>S</sub> Series Inductance	-	12	-	nH	Measured lead to lead 5mm from package body

**Dynamic Recovery Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Parameters	Min	Typ	Max	Units	Test Conditions
t <sub>rr</sub> Reverse Recovery Time	-	-	35	ns	I <sub>F</sub> = 1.0A, di <sub>F</sub> /dt = 50A/μs, V <sub>R</sub> = 30V
	-	22	-		T <sub>J</sub> = 25°C
	-	39	-		T <sub>J</sub> = 125°C
I <sub>R</sub> RRM Peak Recovery Current	-	1.6	-	A	T <sub>J</sub> = 25°C
	-	4.1	-		T <sub>J</sub> = 125°C
Q <sub>rr</sub> Reverse Recovery Charge	-	19	-	nC	T <sub>J</sub> = 25°C
	-	-	90	-	T <sub>J</sub> = 125°C

I<sub>F</sub> = 15A  
V<sub>R</sub> = 160V  
di<sub>F</sub>/dt = 200A/μs

**Thermal - Mechanical Characteristics**

Parameters	Min	Typ	Max	Units
T <sub>J</sub> Max. Junction Temperature Range	-	-	- 65 to 175	°C
T <sub>Stg</sub> Max. Storage Temperature Range	-	-	- 65 to 175	
R <sub>thJC</sub> Thermal Resistance, Junction to Case Per Leg	-	-	1.5	°C/ W
R <sub>thJA</sub> ① Thermal Resistance, Junction to Ambient Per Leg	-	-	40	
R <sub>thCS</sub> ② Thermal Resistance, Case to Heatsink	-	0.5	-	
Wt Weight	-	6.0	-	g
	-	0.21	-	(oz)
Mounting Torque	6.0	-	12	Kg-cm
	5.0	-	10	lbf.in
Marking Device	MUR3020WT			

① Typical Socket Mount

② Mounting Surface, Flat, Smooth and Greased

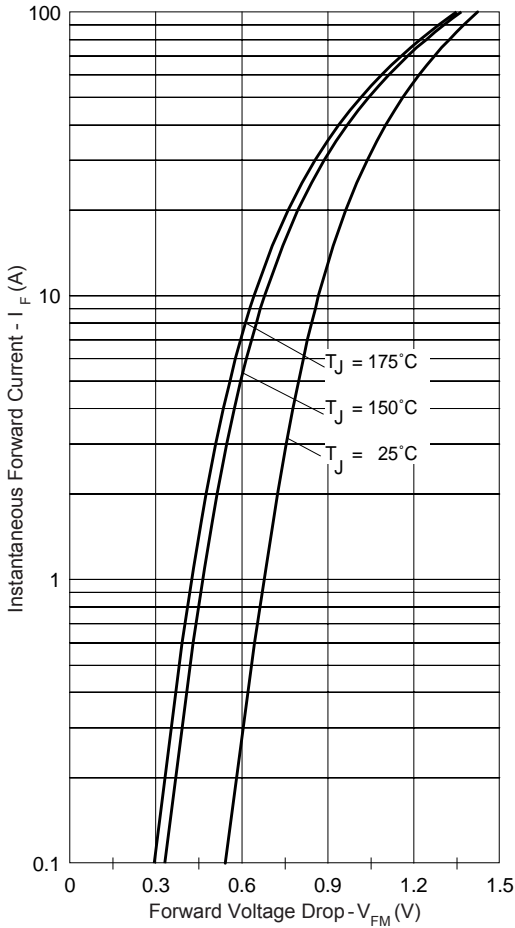


Fig. 1 - Typical Forward Voltage Drop Characteristics

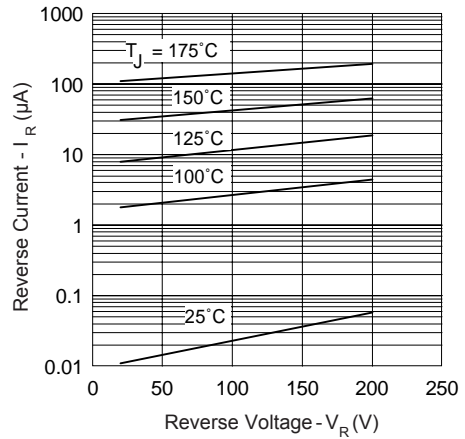


Fig. 2 - Typical Values Of Reverse Current Vs. Reverse Voltage

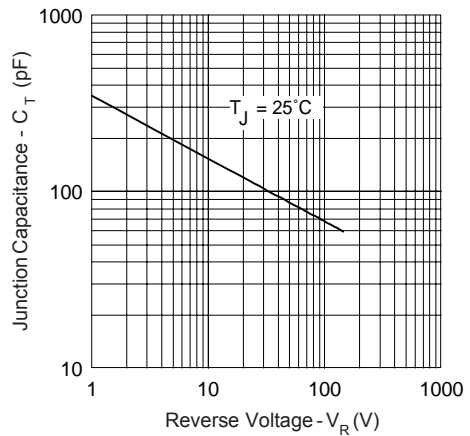


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

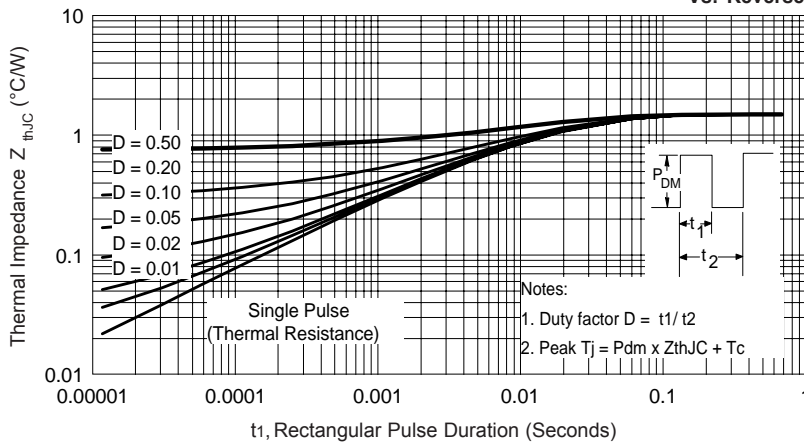


Fig. 4 - Max. Thermal Impedance  $Z_{thJC}$  Characteristics

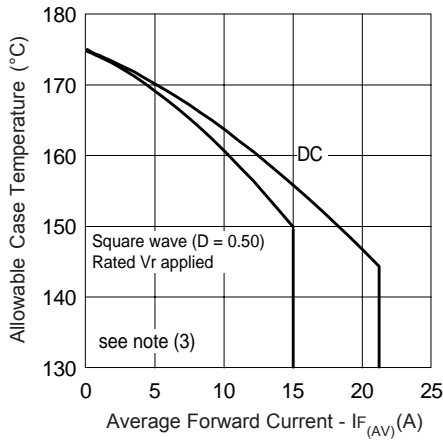


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current

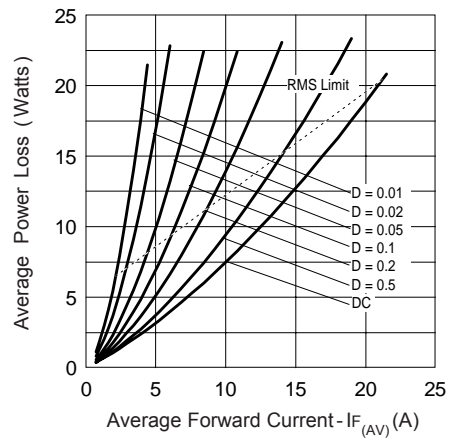


Fig. 6 - Forward Power Loss Characteristics

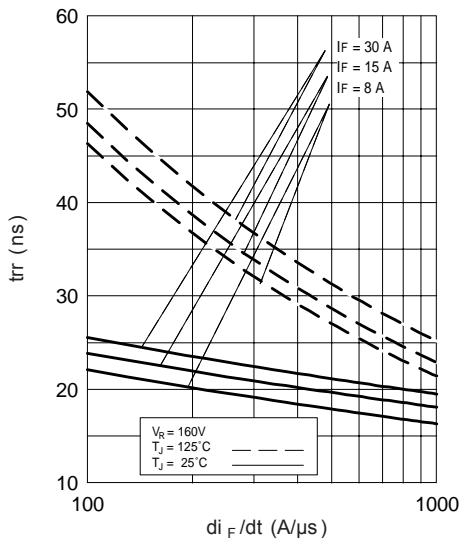


Fig. 7 - Typical Reverse Recovery vs.  $di_F/dt$

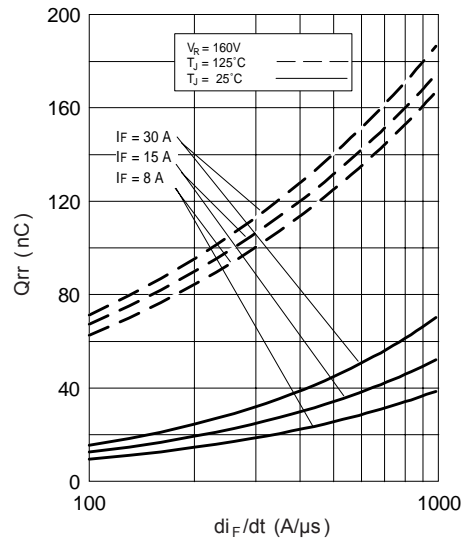


Fig. 8 - Typical Stored Charge vs.  $di_F/dt$

(3) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

$Pd$  = Forward Power Loss =  $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);

$Pd_{REV}$  = Inverse Power Loss =  $V_{R1} \times I_{R1} (1 - D)$ ;  $I_{R1} @ V_{R1}$  = rated  $V_R$

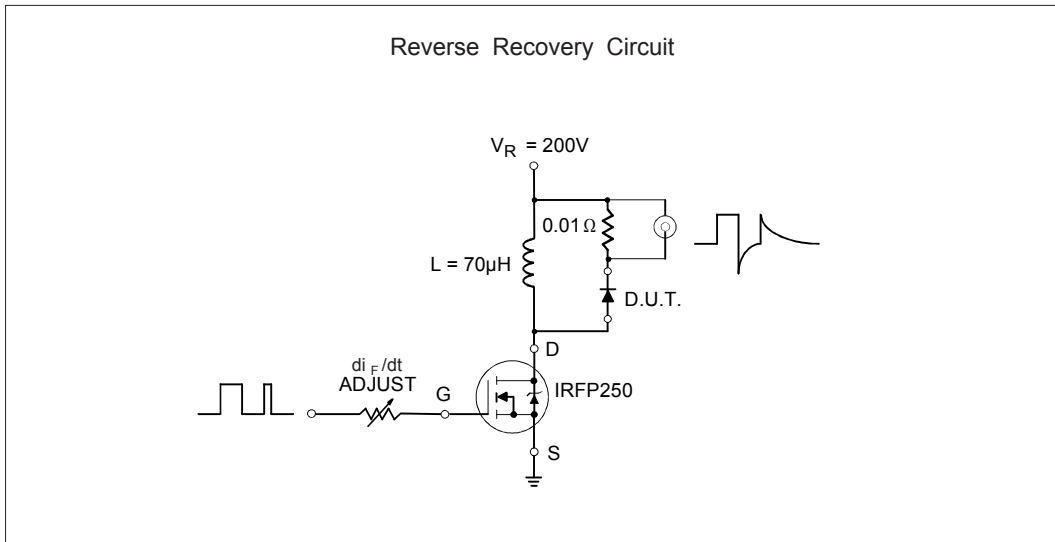


Fig. 9- Reverse Recovery Parameter Test Circuit

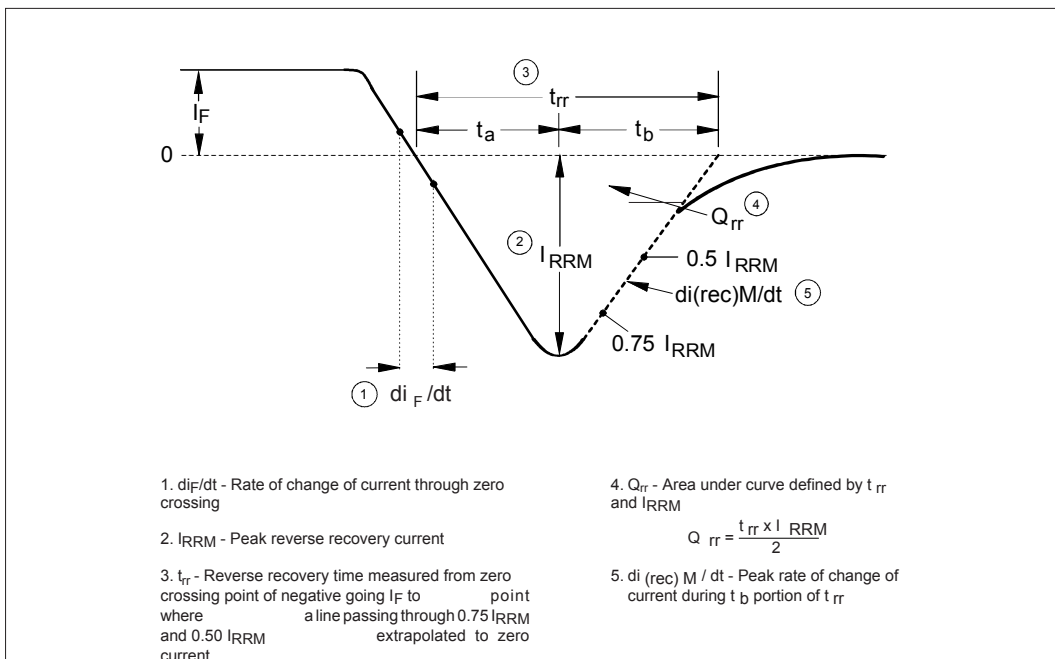
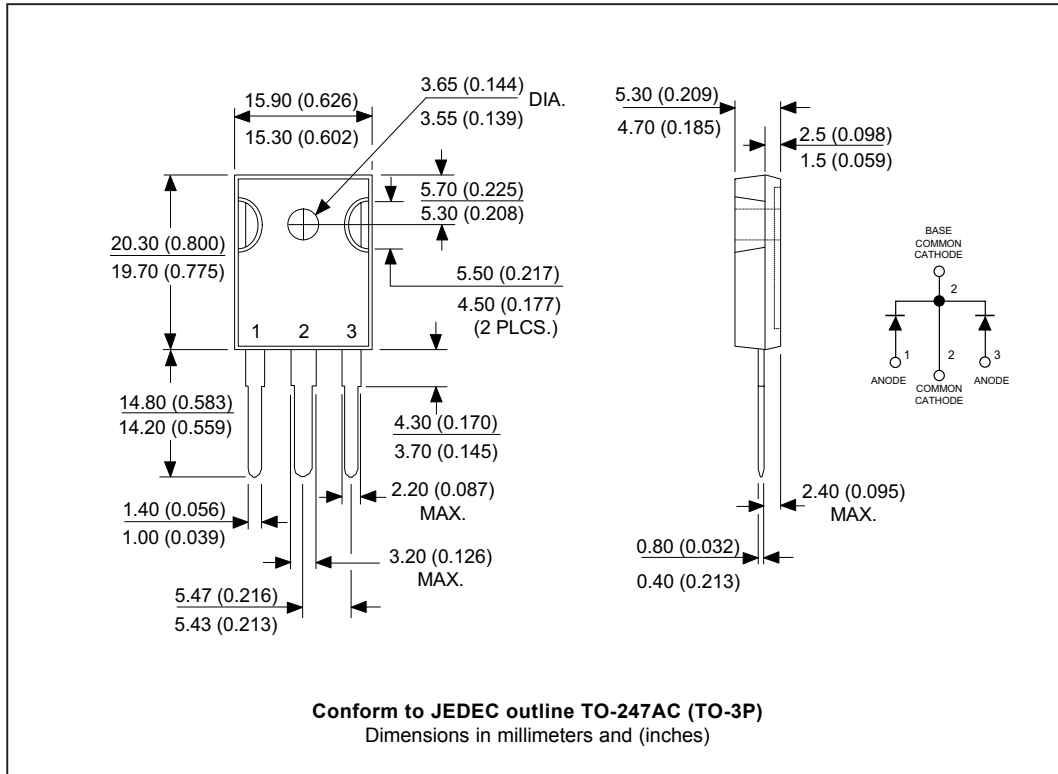
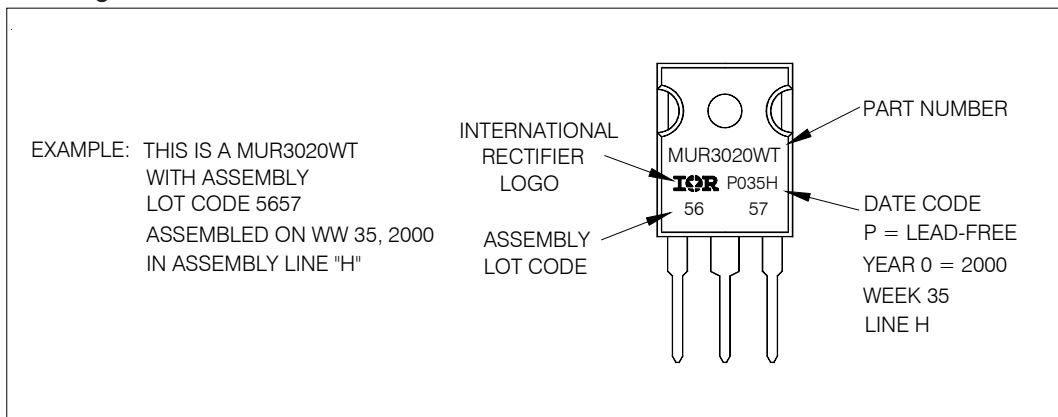


Fig. 10 - Reverse Recovery Waveform and Definitions

Outline Table



Marking Information



### Ordering Information Table

Device Code				
<b>MUR</b>	<b>30</b>	<b>20</b>	<b>WT</b>	<b>PbF</b>
1	2	3	4	5
<b>1</b>	-	Ultrafast MUR Series (TO-247AC)		
<b>2</b>	-	Current Rating (30 = 30A)		
<b>3</b>	-	Voltage Rating (20 = 200V)		
<b>4</b>	-	WT = Center Tap (Dual) TO-247		
<b>5</b>	-	<ul style="list-style-type: none"><li>• none = Standard Production</li><li>• PbF = Lead-Free</li></ul>		

Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial Level and Lead-Free.  
Qualification Standards can be found on IR's Web site.